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**INFORMATION DISCLOSURE
STATEMENT BY APPLICANT**
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Complete if Known

Application Number	Unknown 10/789203
Filing Date	Even Date Herewith
First Named Inventor	Forbes, Leonard
Group Art Unit	Unknown 2815
Examiner Name	Unknown Ecker

Sheet 1 of 11

Attorney Docket No: 303.356US4

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Substitute Disclosure Statement Form (PTO-1449)

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Group Art Unit	Unknown 2B15
Examiner Name	Unknown ECKERT

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Attorney Docket No: 303.356US4

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First Named Inventor	Forbes, Leonard
Group Art Unit	Unknown 2815
Examiner Name	Unknown ECKERT

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Attorney Docket No: 303.356US4

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	First Named Inventor	Forbes, Leonard
	Group Art Unit	Unknown 2B15
	Examiner Name	Unknown ECKERT
Sheet 4 of 11		Attorney Docket No: 303.356US4

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First Named Inventor Forbes, Leonard

Group Art Unit ~~Unknown~~ 285Examiner Name ~~Unknown~~ Eckert

Sheet 5 of 11

Attorney Docket No: 303.356US4

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First Named Inventor	Forbes, Leonard
Group Art Unit	Unknown 2B15
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First Named Inventor	Forbes, Leonard
Group Art Unit	Unknown 2815
Examiner Name	Unknown ECKER

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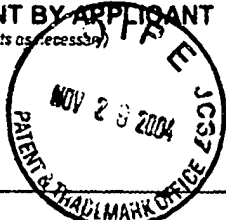
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Filing Date February 27, 2004
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Group Art Unit 2811 2815
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		Filing Date	February 27, 2004
		First Named Inventor	Forbes, Leonard
		Group Art Unit	2811 2015
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Examiner Initial *	USP Document Number	Publication Date	Name of Patentee or Applicant of cited Document	Class	Subclass	Filing Date If Appropriate
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